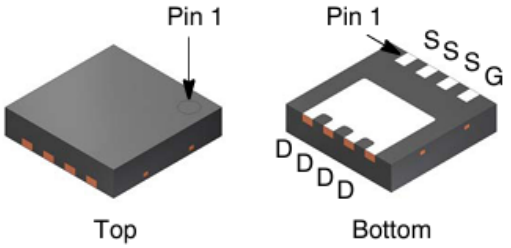
MOSFET – N-Channel, POWERTRENCH®

150 V, 13 A, 90 mΩ

FDMC86248

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
150 V	90 mΩ @ 10 V	13 A
	125 mΩ @ 6 V	



PQFN8 3.3 × 3.3, 0.65P
CASE 483AW

General Description

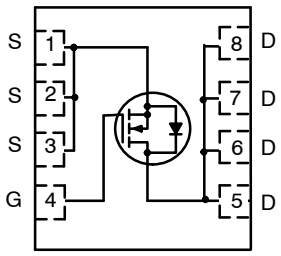
This N-Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that has been especially tailored to minimize the on–state resistance and yet maintain superior switching performance.

Features

- Max $R_{DS(on)}$ = 90 mΩ at V_{GS} = 10 V, I_D = 3.4 A
- Max $R_{DS(on)}$ = 125 mΩ at V_{GS} = 6 V, I_D = 2.9 A
- Advanced Package and Silicon Combination for Low $R_{DS(on)}$ and High Efficiency
- 100% UIL Tested
- Pb–Free, Halide Free and RoHS Compliant

Applications

- Primary MOSFET
- MV Synchronous Rectifier



N-CHANNEL MOSFET

MAXIMUM RATINGS (T_A = 25 °C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V_{DS}	Drain to Source Voltage	150	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current – Continuous (T_C = 25 °C) – Continuous (Note 1a) (T_A = 25 °C) – Pulsed	 13 3.4 15	A
E_{AS}	Single Pulse Avalanche Energy (Note 3)	37	mJ
P_D	Power Dissipation (T_C = 25 °C) Power Dissipation (Note 1a) (T_A = 25 °C)	36 2.3	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted.)

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	°C/W

MARKING DIAGRAM



Z = Assembly Plant Code
XYY = 3–Digit Date Code Format
KK = 2–Alphanumeric Lot Run Traceability Code
FDMC86248 = Specific Device Code

ORDERING INFORMATION

Device	Package	Shipping†
FDMC86248	PQFN8 (Pb–Free, Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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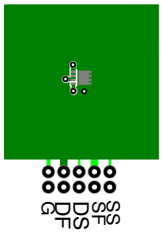
ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	150	–	–	V
ΔBV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C	–	104	–	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V	–	–	1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	3.2	4.0	V
$\Delta V_{GS(th)}$ /ΔT_J	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C	–	–9	–	mV/°C
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 3.4 A	–	69	90	mΩ
		V_{GS} = 6 V, I_D = 2.9 A	–	89	125	
		V_{GS} = 10 V, I_D = 3.4 A, T_J = 125 °C	–	140	183	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 3.4 A	–	10	–	S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz	–	393	525	pF
C_{oss}	Output Capacitance		–	50	70	pF
C_{rss}	Reverse Transfer Capacitance		–	2.6	5.0	pF
R_g	Gate Resistance		–	0.8	2.0	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75 V, I_D = 3.4 A, V_{GS} = 10 V, R_{GEN} = 6 Ω	–	6.9	14	ns
t_r	Rise Time		–	1.4	10	ns
$t_{d(off)}$	Turn-Off Delay Time		–	11	20	ns
t_f	Fall Time		–	2.8	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V, V_{DD} = 75 V, I_D = 3.4 A	–	6.4	9.0	nC
		V_{GS} = 0 V to 5 V, V_{DD} = 75 V, I_D = 3.4 A	–	3.7	5.2	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 75 V, I_D = 3.4 A	–	1.9	–	nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 75 V, I_D = 3.4 A	–	1.7	–	nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 3.4 A (Note 2)	–	0.80	1.3	V
		V_{GS} = 0 V, I_S = 2 A (Note 2)	–	0.78	1.2	
t_{rr}	Reverse Recovery Time	I_F = 3.4 A, di/dt = 100 A/μs	–	54	86	ns
Q_{rr}	Reverse Recovery Charge		–	48	77	nC

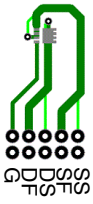
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user’s board design.



a) 53 °C/W when mounted on a 1 in^2 pad of 2 oz. copper.



b) 125 °C/W when mounted on a minimum pad of 2 oz. copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 37 mJ is based on starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 5 A, V_{DD} = 150 V, V_{GS} = 10 V. 100% test at L = 0.3 mH, I_{AS} = 12 A.

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TYPICAL CHARACTERISTICS

(T_J = 25 °C unless otherwise noted)

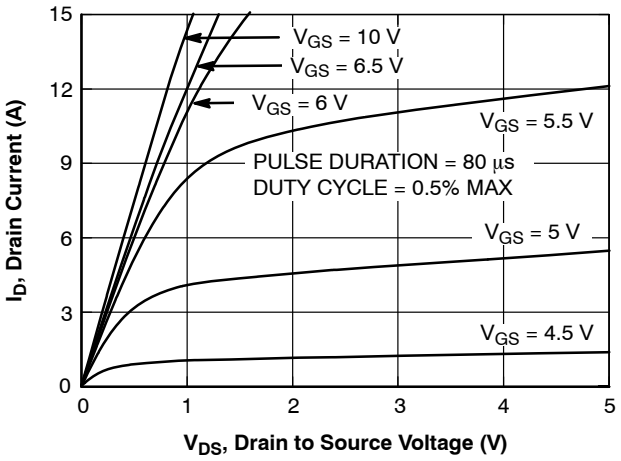


Figure 1. On−Region Characteristics

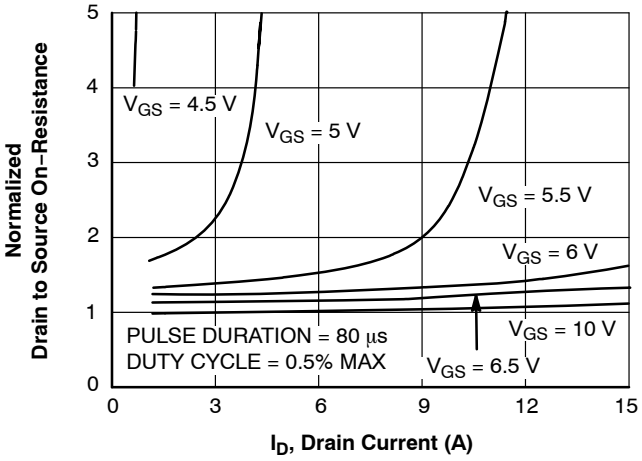


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

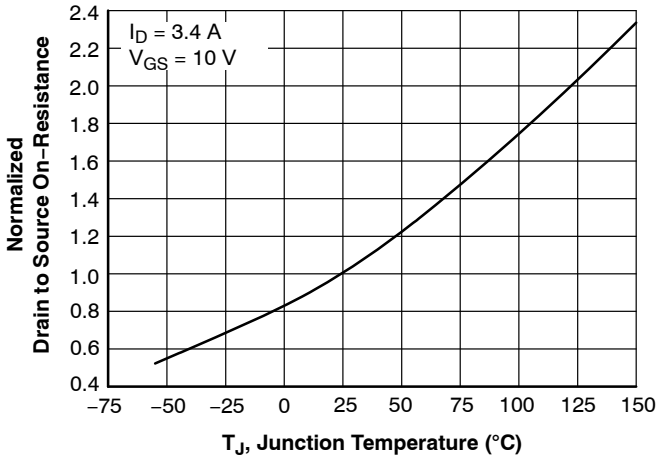


Figure 3. Normalized On−Resistance vs. Junction Temperature

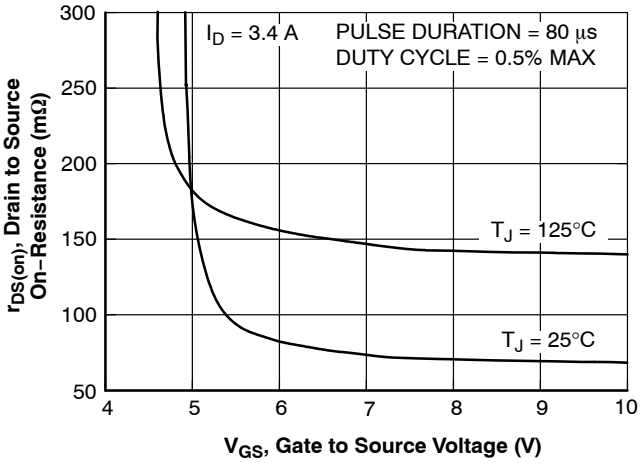


Figure 4. On−Resistance vs. Gate to Source Voltage

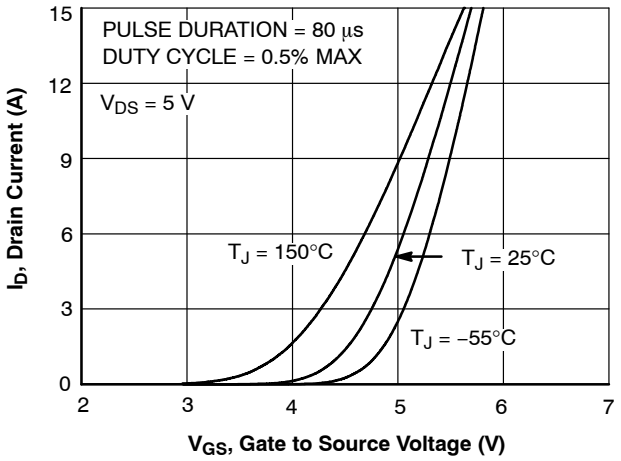


Figure 5. Transfer Characteristics

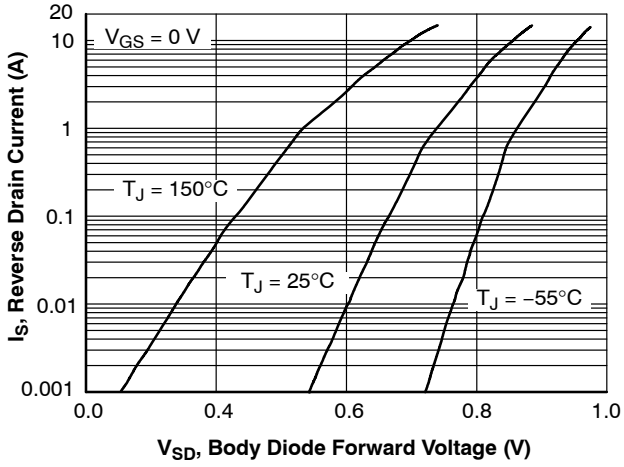


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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TYPICAL CHARACTERISTICS (continued)

(T_J = 25 °C unless otherwise noted)

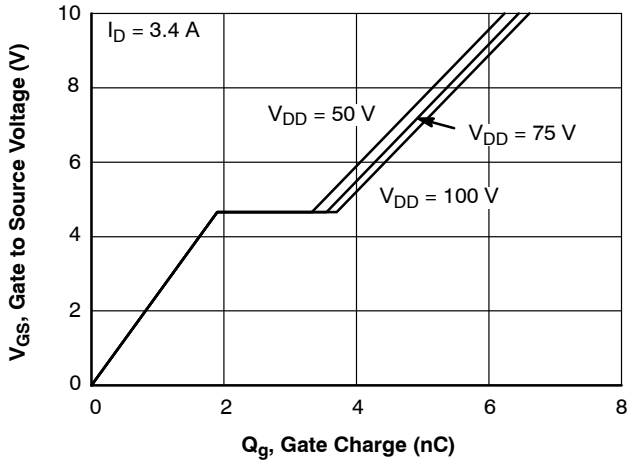


Figure 7. Gate Charge Characteristics

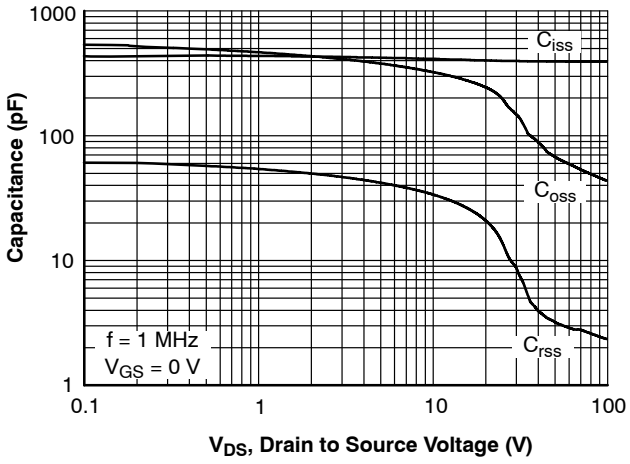


Figure 8. Capacitance vs. Drain to Source Voltage

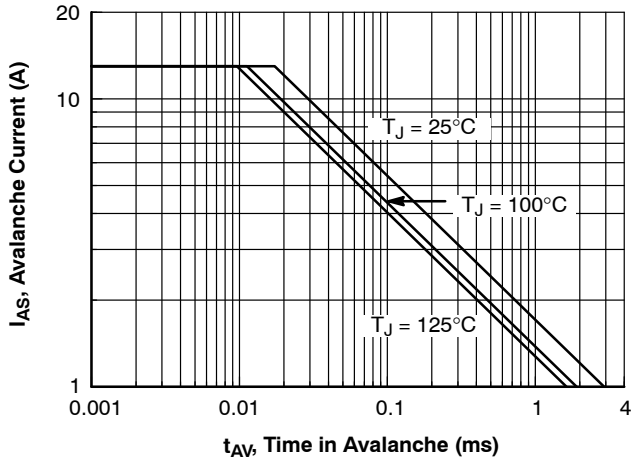


Figure 9. Unclamped Inductive Switching Capability

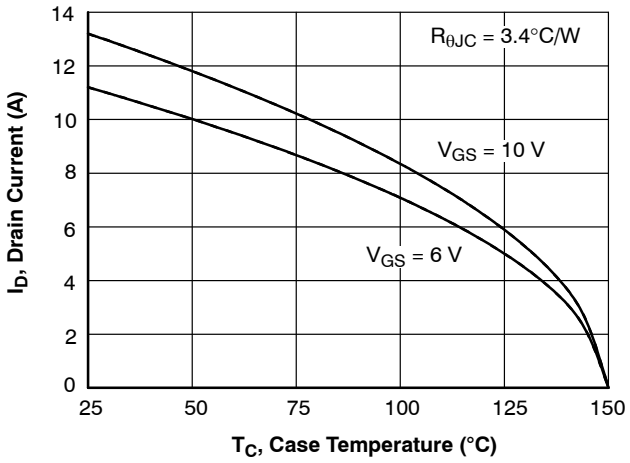


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

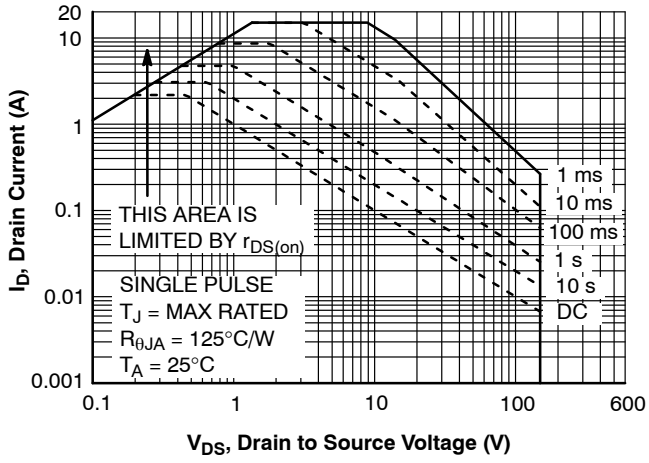


Figure 11. Forward Bias Safe Operating Area

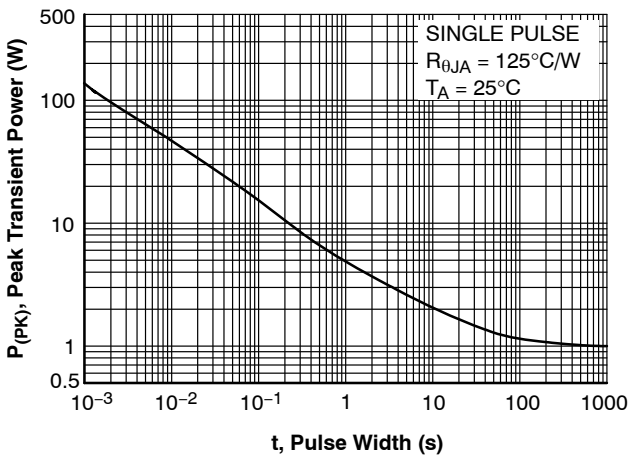


Figure 12. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS (continued)

(T_J = 25 °C unless otherwise noted)

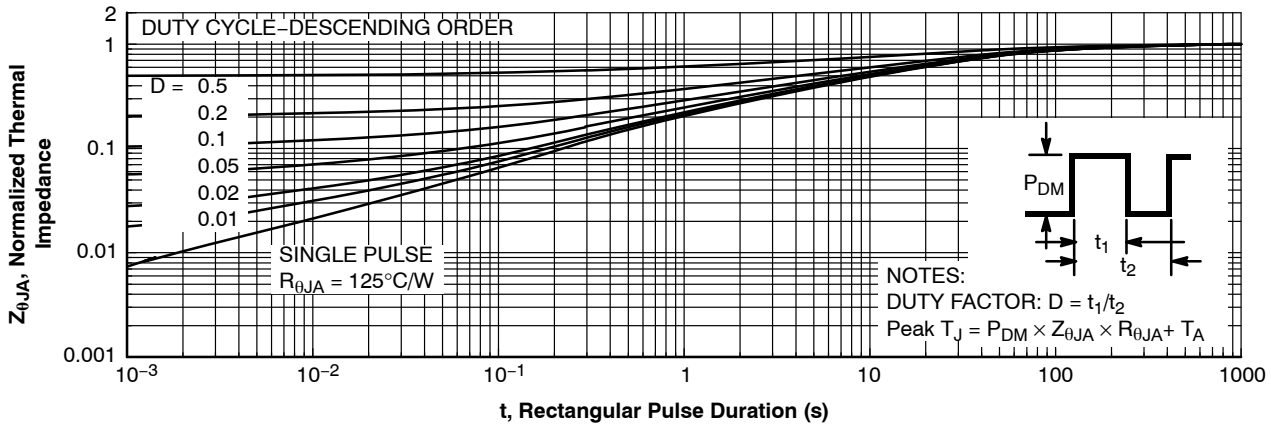


Figure 13. Junction−to−Ambient Transient Thermal Response Curve

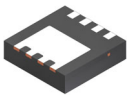
REVISION HISTORY

Revision	Description of Changes	Date
4	Changed package outline drawing from 483AK to 483AW.	5/12/2026

* Please note that this document has been previously updated prior to the inclusion of this revision history table and that the changes tracked only reflect what has occurred on the noted approval dates.

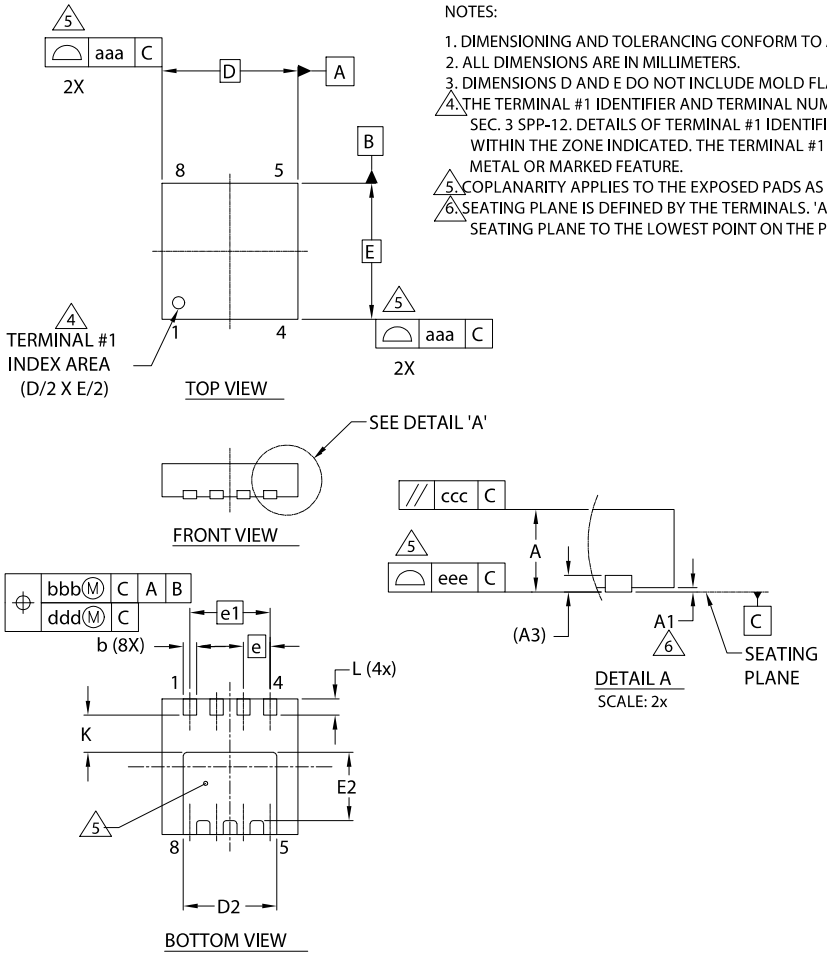
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WDFN−8 3.30x3.30x0.75, 0.65P
CASE 483AW
ISSUE C

DATE 25 SEP 2026



NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
4. THE TERMINAL #1 IDENTIFIER AND TERMINAL NUMBERING CONVENTION SHALL CONFORM TO JEP95 SEC. 3 SPP-12. DETAILS OF TERMINAL #1 IDENTIFIER ARE OPTIONAL, BUT MUST BE LOCATED WITHIN THE ZONE INDICATED. THE TERMINAL #1 IDENTIFIER MAY BE EITHER A MOLD, EMBEDDED METAL OR MARKED FEATURE.
5. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. 'A1' IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

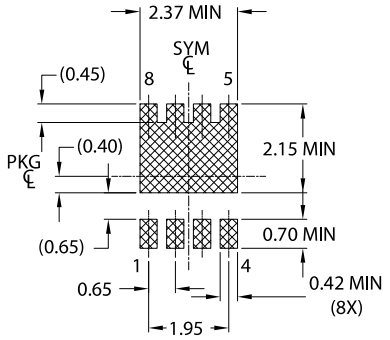
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	–	–	0.05
A3		0.20 REF	
b	0.27	0.32	0.37
D		3.30 BSC	
D2	2.17	2.27	2.37
E		3.30 BSC	
E2	1.56	1.66	1.76
e		0.65 BSC	
e1		1.95 BSC	
K	0.90	–	--
L	0.30	0.40	0.50
aaa		0.10	
bbb		0.10	
ccc		0.10	
ddd		0.05	
eee		0.05	

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques reference manual, SOLDERRM/D.

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DESCRIPTION:	**WDFN−8 3.30x3.30x0.75, 0.65P**	**PAGE 1 OF 1**

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